

Title (en)
METHOD OF FORMING LOW-DIELECTRIC-CONSTANT AMORPHOUS SILICA COATING AND LOW-DIELECTRIC-CONSTANT AMORPHOUS SILICA COATING OBTAINED BY THE METHOD

Title (de)
VERFAHREN ZUR HERSTELLUNG EINER BESCHICHTUNG AUS AMORPHEM SILIZIUMOXID MIT NIEDRIGER DIELEKTRIZITATSKONSTANTE UND DURCH DIESES VERFAHREN ERHALTENE BESCHICHTUNG AUS AMORPHEM SILIZIUMOXID MIT NIEDRIGER DIELEKTRIZITATSKONSTANTE

Title (fr)
PROCEDE DE FABRICATION D'UN REVETEMENT DE SILICE AMORPHE A FAIBLE CONSTANCE DIELECTRIQUE ET REVETEMENT AINSI OBTENU

Publication
EP 1564798 B1 20170802 (EN)

Application
EP 03758926 A 20031027

Priority
• JP 0313691 W 20031027
• JP 2002318418 A 20021031

Abstract (en)
[origin: EP1564798A1] The present invention relates to an amorphous silica-based coating film with a low specific dielectric constant of 2.5 or below and the Young' s modulus of 6.0 GPa or more and having excellent hydrophobic property, and to a method of forming the same. A liquid composition containing a silicon compound obtained by hydrolyzing tetraalkyl ortho silicate (TAOS) and specific alkoxysilane (AS) in the presence of tetraalkyl ammonium hydroxide (TAAOH) is prepared. The liquid composition is then applied on a substrate, heated and cured to obtain a coating film. The coating film obtained as described has a smooth surface and also has specific micropores therein. <IMAGE>

IPC 8 full level
H01L 21/312 (2006.01); **C08G 77/08** (2006.01); **C09D 183/02** (2006.01); **C09D 183/04** (2006.01); **H01L 21/316** (2006.01)

CPC (source: EP KR US)
C08G 77/08 (2013.01 - EP KR US); **C09D 183/02** (2013.01 - EP KR US); **H01L 21/02126** (2013.01 - KR US); **H01L 21/02203** (2013.01 - KR US); **H01L 21/02216** (2013.01 - KR US); **H01L 21/02282** (2013.01 - KR US); **H01L 21/02337** (2013.01 - EP KR US); **H01L 21/316** (2013.01 - US); **H01L 21/31695** (2013.01 - US); **H01L 21/324** (2013.01 - KR); **H01L 21/02126** (2013.01 - EP); **H01L 21/02203** (2013.01 - EP); **H01L 21/02216** (2013.01 - EP); **H01L 21/02282** (2013.01 - EP)

Cited by
EP1786028A1; EP1814150A4; EP1813655A4; US7830013B2

Designated contracting state (EPC)
DE IT NL

DOCDB simple family (publication)
EP 1564798 A1 20050817; **EP 1564798 A4 20060118**; **EP 1564798 B1 20170802**; CN 100380608 C 20080409; CN 1708839 A 20051214; JP 2004153147 A 20040527; JP 4225765 B2 20090218; KR 100983426 B1 20100920; KR 20050060108 A 20050621; TW 200500494 A 20050101; TW I280263 B 20070501; US 2006084277 A1 20060420; US 7232769 B2 20070619; WO 2004040635 A1 20040513

DOCDB simple family (application)
EP 03758926 A 20031027; CN 200380102612 A 20031027; JP 0313691 W 20031027; JP 2002318418 A 20021031; KR 20057007529 A 20031027; TW 92130290 A 20031030; US 53323805 A 20050616